

N-Channel Enhancement Mode MOSFET

Typical Characteristics

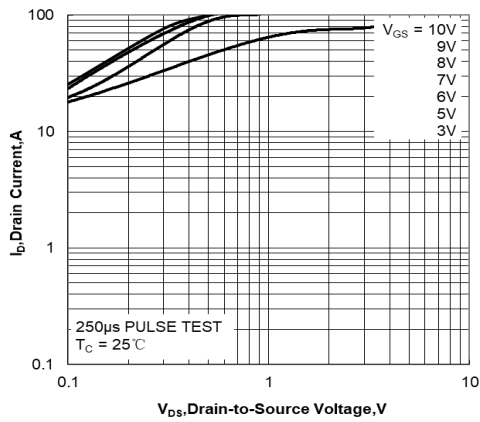


Figure 1. Output Characteristics

Figure 2. Transfer Characteristics

Figure 3. Drain-to-Source On Resistance vs Drain Current

Figure 4. Body Diode Forward Voltage vs Source Current and Temperature

Figure . Maximum Continuous Drain Current vs Case Temperature

Figure . Maximum Power Dissipation vs Case Temperature

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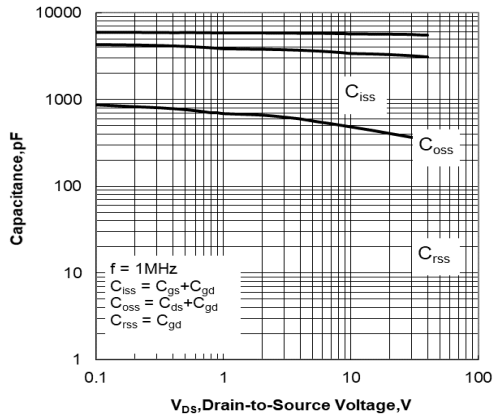


Figure 7. Capacitance Characteristics

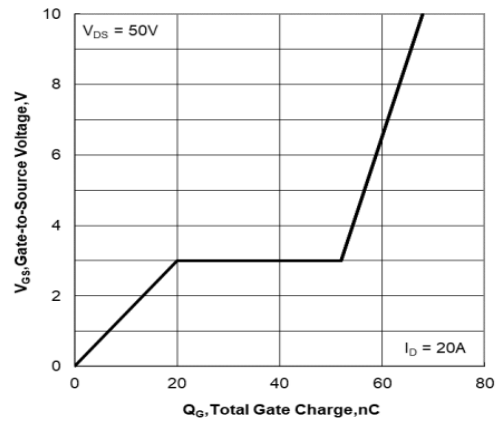


Figure 8. Gate Charge Characteristics

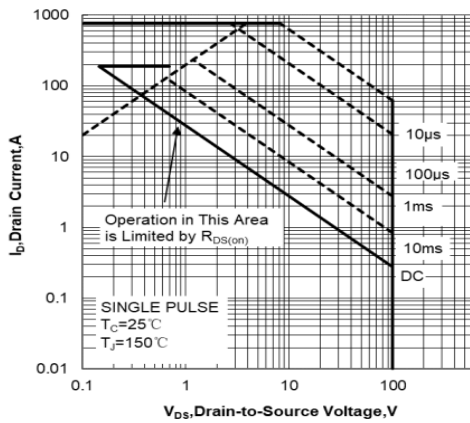


Figure 9. Maximum Safe Operating Area

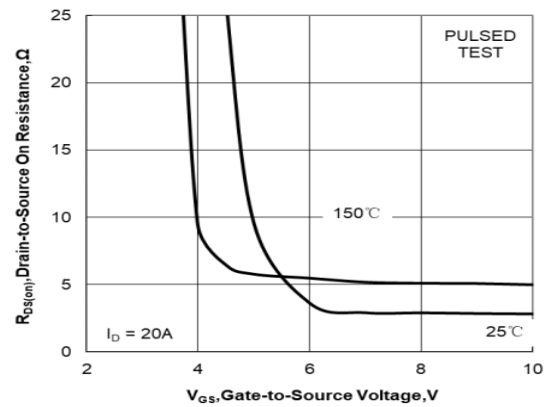


Figure 10. Drain-to-Source On Resistance vs Gate Voltage and Drain Current

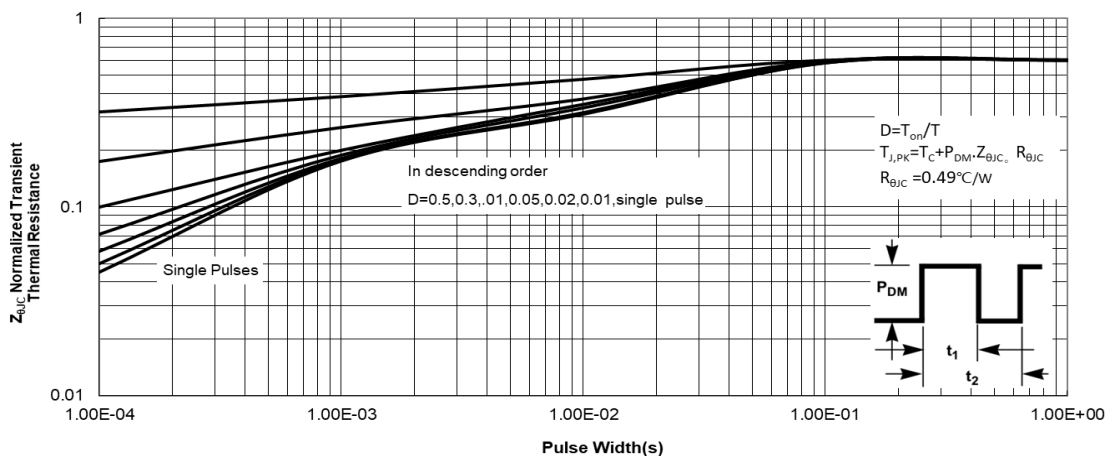
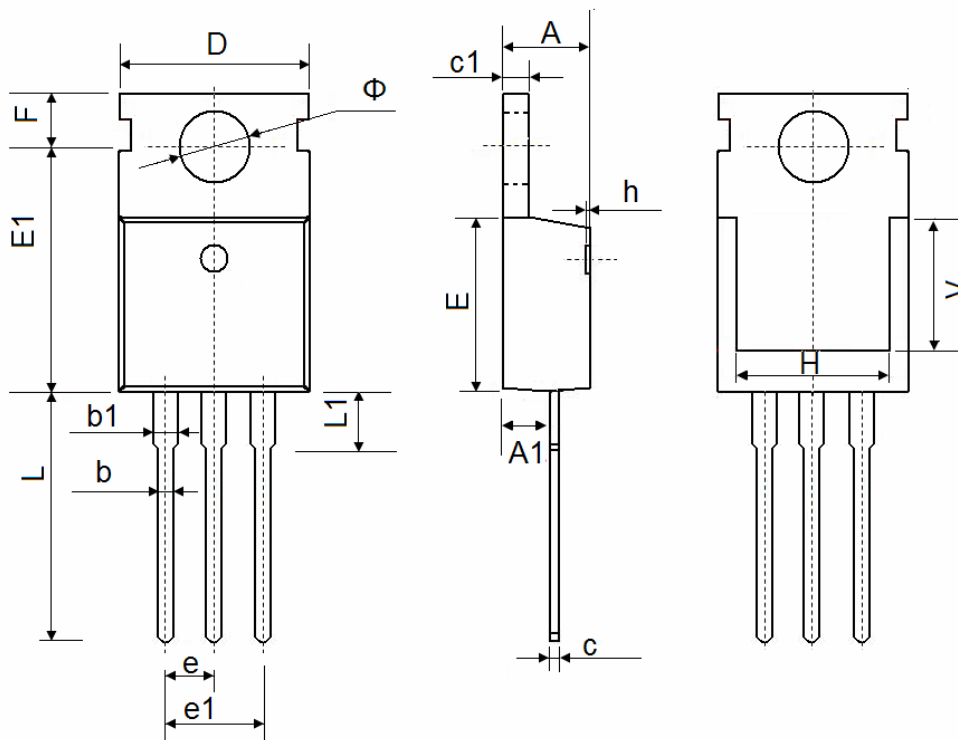


Figure 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case

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TO-220 Package Outline Data


Symbol	Dimensions In Millimeters	
	Min.	Max.
A	4.350	4.650
A1	2.250	2.550
b	0.710	0.910
b1	1.170	1.400
c	0.330	0.650
c1	1.200	1.400
D	9.910	10.250
E	8.9500	9.750
E1	12.650	12.950
e	2.540 TYP.	
e1	4.980	5.180
F	2.650	2.950
H	7.900	8.100
h	0.000	0.300
L	12.700	13.500
L1	2.850	3.250
V	7.500 REF.	
Φ	3.400	3.800